TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

# 2SA1832FT

Audio frequency General Purpose Amplifier Applications

Unit: mm

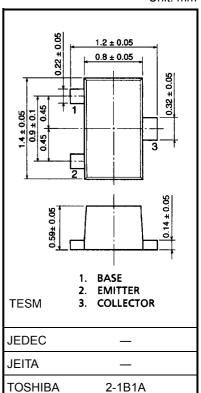
- High voltage:  $V_{CEO} = -50 \text{ V}$
- High current:  $I_C = -150 \text{ mA} \text{ (max)}$
- High hFE: hFE = 120 to 400
- Excellent hFE linearity

 $h_{\rm FE}$  (IC = -0.1 mA)/h<sub>FE</sub> (IC = -2 mA) = 0.95 (typ.)

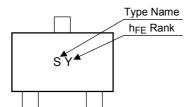
• Complementary to 2SC4738F

#### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-150	mA
Base current	Ι <sub>Β</sub>	-30	mW
Collector power dissipation	P <sub>C</sub>	100	mW
Junction temperature	Тј	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to 125	°C



## Marking



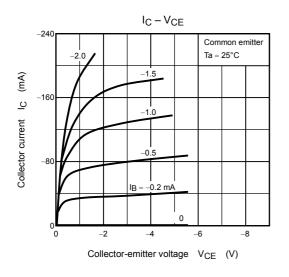
# **Electrical Characteristics (Ta = 25°C)**

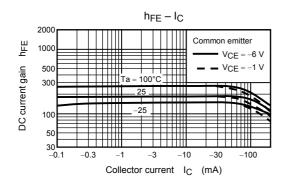
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -5 V, I_C = 0$			-0.1	μA
DC current gain	h <sub>FE</sub> (Note)	$V_{CE} = -6 \text{ V}, \text{ I}_{B} = -2 \text{ mA}$	120	_	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{\rm C} = -100$ mA, $I_{\rm B} = -10$ mA	_	-0.1	-0.3	V
Transition frequency	fT	$V_{CE} = -10 \text{ V}, \text{ I}_{C} = -1 \text{ mA}$	80			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	4	7	pF

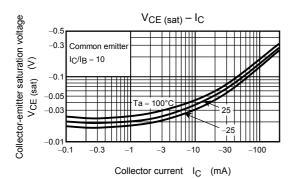
Note: hFE Classification Y (Y): 120 to 140, GR (G): 200 to 400

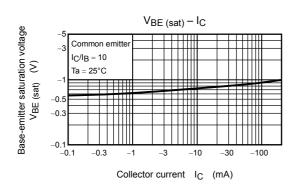
( ) Marking symbol

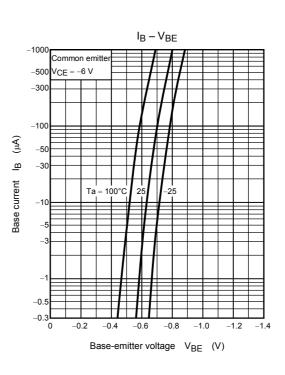
# TOSHIBA



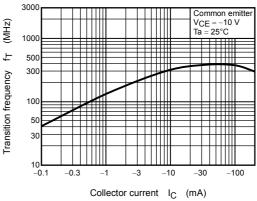


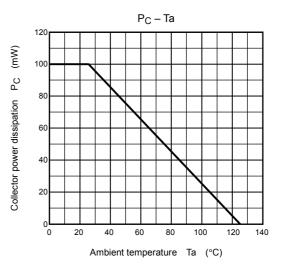












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